

Data sheet acquired from Harris Semiconductor SCHS188C

High-Speed CMOS Logic Octal D-Type Flip-Flop, Three-State Inverting Positive-Edge Triggered

January 1998 - Revised April 2004

Features

- Buffered Inputs
- Common Three-State Output-Enable Control
- Three-State Outputs
- . Bus Line Driving Capability
- Typical Propagation Delay = 13ns at V_{CC} = 5V,
 C_L = 15pF, T_A = 25°C (Clock to Output)
- Fanout (Over Temperature Range)
 - Standard Outputs...... 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility,
 V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)

Description

The 'HC534, 'HCT534, 'HC564, and 'HCT564 are high speed Octal D-Type Flip-Flops manufactured with silicon gate CMOS technology. They possess the low power consumption of standard CMOS integrated circuits, as well as the ability to drive 15 LSTTL loads. Due to the large output drive capability and the three-state feature, these devices are ideally suited for interfacing with bus lines in a bus organized system. The two types are functionally identical and differ only in their pinout arrangements.

The 'HC534, 'HCT534, 'HC564, and 'HCT564 are positive edge triggered flip-flops. Data at the D inputs, meeting the setup and hold time requirements, are inverted and transferred to the Q outputs on the positive going transition of the CLOCK input. When a high logic level is applied to the OUT-PUT ENABLE input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements.

The HCT logic family is speed, function, and pin compatible with the standard LS logic family.

Ordering Information

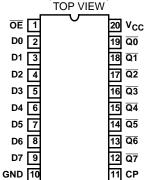
PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC534F3A	-55 to 125	20 Ld CERDIP
CD54HC564F3A	-55 to 125	20 Ld CERDIP
CD54HCT534F3A	-55 to 125	20 Ld CERDIP
CD54HCT564F3A	-55 to 125	20 Ld CERDIP
CD74HC534E	-55 to 125	20 Ld PDIP
CD74HC564E	-55 to 125	20 Ld PDIP
CD74HC564M	-55 to 125	20 Ld SOIC
CD74HC564M96	-55 to 125	20 Ld SOIC
CD74HCT534E	-55 to 125	20 Ld PDIP
CD74HCT564E	-55 to 125	20 Ld PDIP
CD74HCT564M	-55 to 125	20 Ld SOIC

Pinouts

CD54HC534, CD54HCT534 (CERDIP)
CD74HC534, CD74HCT534
(PDIP)
TOP VIEW OE 1 20 V_{CC} $\overline{\mathbf{Q0}}$ 19 Q7 D0 18 D7 17 D6 D1 Q1 16 Q6 Q2 6 15 Q5 14 D5 D2 D3 8 13 D4 Q3 12 Q4

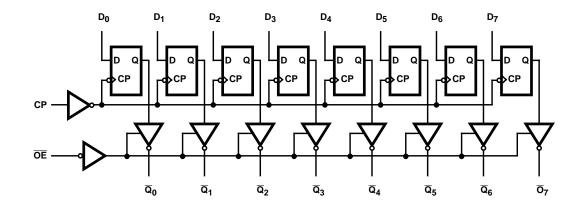
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CD54HC564, CD54HCT564 (CERDIP) CD74HC564, CD74HCT564 (PDIP, SOIC) TOP VIEW



Functional Diagram

GND 10



TRUTH TABLE

	INPUTS		OUTPUT
ŌĒ	СР	Dn	Qn
L	↑	Н	L
L	1	L	Н
L	L	Х	No Change
Н	Х	Х	Z

H = High Level (Steady State)

L = Low Level (Steady State)

X= Don't Care

↑= Transition from Low to High Level

Z = High Impedance State

Absolute Maximum Ratings

DC Supply Voltage, V $_{CC}$... -0.5V to 7V DC Input Diode Current, I $_{IK}$ For V $_{I}$ < -0.5V or V $_{I}$ > V $_{CC}$ + 0.5V ... ± 20 mA DC Output Diode Current, I $_{OK}$ For V $_{O}$ < -0.5V or V $_{O}$ > V $_{CC}$ + 0.5V ... ± 20 mA DC Drain Current, per Output, I $_{O}$ For -0.5V < V $_{O}$ < V $_{CC}$ + 0.5V ... ± 35 mA DC Output Source or Sink Current per Output Pin, I $_{O}$ For V $_{O}$ > -0.5V or V $_{O}$ < V $_{CC}$ + 0.5V ... ± 25 mA DC V $_{CC}$ or Ground Current, I $_{CC}$... ± 50 mA

Thermal Information

Thermal Resistance (Typical, Note 1) θ_{JA}	(oC/W)
E (PDIP) Package	. 69
M (SOIC) Package	
Maximum Junction Temperature	150 ⁰ C
Maximum Storage Temperature Range65°C	c to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(SOIC - Lead Tips Only)	

Operating Conditions

Temperature Range, T _A 55°C to 125°C
Supply Voltage Range, V _{CC}
HC Types2V to 6V
HCT Types
DC Input or Output Voltage, V _I , V _O 0V to V _{CC}
Input Rise and Fall Time
2V
4.5V 500ns (Max)
6V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. The package impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

		TES CONDI		V _{CC}		25°C		-40°C T	O 85°C	-55°C TO 125°C							
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS					
HC TYPES																	
High Level Input	V _{IH}	-	-	2	1.5	i	-	1.5	-	1.5	-	V					
Voltage				4.5	3.15	•	-	3.15	-	3.15	-	V					
				6	4.2	-	-	4.2	-	4.2	-	V					
Low Level Input	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V					
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	V					
				6	-	-	1.8	-	1.8	-	1.8	V					
High Level Output	V _{OH}	V _{IH} or V _{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V					
Voltage CMOS Loads			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V					
OWO Edda			-0.02	6	5.9	-	-	5.9	-	5.9	-	V					
High Level Output	1							-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V					
112 20000			-7.8	6	5.48	-	-	5.34	-	5.2	-	V					
Low Level Output	V _{OL}	V _{IH} or V _{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V					
Voltage CMOS Loads			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V					
			0.02	6	-	-	0.1	-	0.1	-	0.1	V					
Low Level Output	1		-	-	-	-	-	-	-	-	-	V					
Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V					
			7.8	6	-	-	0.26	-	0.33	-	0.4	V					
Input Leakage Current	Ι _Ι	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μА					

DC Electrical Specifications (Continued)

		TES CONDI		V _{CC}		25°C		-40°C 1	O 85°C	-55°C T	O 125°C	
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Quiescent Device Current	Icc	V _{CC} or GND	0	6	-	-	8	-	80	-	160	μΑ
Three- State Leakage Current	V _{IL} or V _{IH}	V _O =V _{CC} or GND	-	6	-	-	±0.5	-	±5.0	-	±10	μΑ
HCT TYPES							•					
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{ОН}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} and GND	0	5.5	-		±0.1	-	±1	-	±1	μΑ
Quiescent Device Current	Icc	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μΑ
Three- State Leakage Current	V _{IL} or V _{IH}	V _O =V _{CC} or GND	-	5.5	-	-	±0.5	-	±5.0	-	±10	μΑ
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI _{CC} (Note 2)	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μΑ

NOTE:

HCT Input Loading Table

INPUT	UNIT LOADS					
D0 - D7	0.15					
СР	0.30					
ŌĒ	0.55					

NOTE: Unit Load is ΔI_{CC} limit specific in DC Electrical Specifications Table, e.g., 360µA max. at $25^{0}C.$

^{2.} For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

Prerequisite for Switching Specifications

				25°C		-40	°C TO 8	5°C	-55 ^c	C TO 12	5°C	UNITS
PARAMETER	SYMBOL	V _{CC} (V)	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
HC TYPES							•					•
Maximum Clock	f _{MAX}	2	6	-	-	5	-	-	4	-	-	MHz
Frequency		4.5	30	-	-	25	-	-	20	-	-	MHz
		6	35	-	-	29	-	-	23	-	-	MHz
Clock Pulse Width	t _W	2	80	-	-	100	-	-	120	-	-	ns
		4.5	16	-	-	20	-	-	24	-	-	ns
		6	14	-	-	17	-	-	20	-	-	ns
Setup Time	t _{SU}	2	60	-	-	75	-	-	90	-	-	ns
Data to Clock		4.5	12	-	-	15	-	-	18	-	-	ns
		6	10	-	-	13	-	-	15	-	-	ns
Hold Time	t _H	2	5	-	-	5	-	-	5	-	-	ns
Data to Clock		4.5	5	-	-	5	-	-	5	-	-	ns
		6	5	-	-	5	-	-	5	-	-	ns
HCT TYPES	•			•	•		•			•		
Maximum Clock Frequency	f _{MAX}	4.5	25	-	-	20	-	-	16	-	-	MHz
Clock Pulse Width	t _W	4.5	20	-	-	25	-	-	30	-	-	ns
Setup Time Data to Clock	t _{SU}	4.5	20	-	-	25	-	-	30	-	-	ns
Hold Time Data to Clock (534)	t _H	4.5	5	-	-	5	-	-	5	-	-	ns
Hold Time Data to Clock (564)	t _H	4.5	3	-	-	3	-	-	3	-	-	ns

Switching Specifications $C_L = 50pF$, Input t_r , $t_f = 6ns$

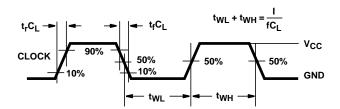
		TEST		TEST		TEST		TEST			25°C			-40°C TO 85°C		-55°C TO 125°C	
PARAMETER	SYMBOL	CONDITIONS	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS						
HC TYPES											-						
Propagation Delay Clock to Output	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	165	-	205	-	250	ns						
			4.5	-	-	33	-	41	-	50	ns						
		C _L = 15pF	5	-	13	-	-	-	-	-	ns						
		C _L = 50pF	6	-	-	28	-	35	-	43	ns						
Output Disable to Q (534)	t _{PLZ} , t _{PHZ}	C _L = 50pF	2	-	-	150	-	190	-	225	ns						
			4.5	-	-	30	-	38	-	45	ns						
		C _L = 15pF	5	-	12	-	-	-	-	-	ns						
		C _L = 50pF	6	-	-	26	-	33	-	38	ns						

Switching Specifications $C_L = 50pF$, Input t_r , $t_f = 6ns$ (Continued)

		TEST			25°C	5°C		С ТО °С	-55°C TO 125°C		
PARAMETER	SYMBOL	CONDITIONS	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Output Disable to Q (564)	t _{PLZ} , t _{PHZ}	C _L = 50pF	2	-	-	135	-	170	-	205	ns
			4.5	-	-	27	-	34	-	41	ns
		C _L = 15pF	5	-	12	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	23	-	29	-	35	ns
Output Enable to Q	t _{PZL} , t _{PZH}	C _L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		C _L = 15pF	5	-	12	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	26	-	33	-	38	ns
Maximum Clock Frequency	f _{MAX}	C _L = 15pF	5	-	60	-	-	-	-	-	MHz
Output Transition Time	t _{THL} , t _{TLH}	C _L = 50pF	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	C _I	C _L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	CO	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C _{PD}	-	5	-	32	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay	t _{PHL} , t _{PLH}										
Clock to Output		$C_L = 50pF$	4.5	-	-	35	-	44	-	53	ns
		C _L = 15pF	5	-	14	-	-	-	-	-	ns
Output Disable to Q	t _{PLZ} , t _{PHZ}	$C_L = 50pF$	4.5	-	-	30	-	38	-	45	ns
		C _L = 15pF	5	1	12	-	ı	-	-	-	ns
Output Enable to Q	t _{PZL} , t _{PZH}	$C_L = 50pF$	4.5	1	-	35	-	44	-	53	ns
		C _L = 15pF	5	-	14	-	-	-	-	-	ns
Maximum Clock Frequency	f _{MAX}	C _L = 15pF	5	1	50	-	-	-	-	-	MHz
Output Transition Time	t _{TLH} , t _{THL}	C _L = 50pF	4.5	1	-	12	-	15	-	18	ns
Input Capacitance	Cl	C _L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	CO	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C _{PD}	-	5	ı	36	-	-	-	-	-	pF

- 3. C_{PD} is used to determine the dynamic power consumption, per package.
 4. P_D = C_{PD} V_{CC}² f_i + ∑ C_L V_{CC}² f_O where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms



NOTE: Outputs should be switching from 10% V $_{CC}$ to 90% V $_{CC}$ in accordance with device truth table. For f $_{MAX}$, input duty cycle = 50%.

FIGURE 1. HC CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

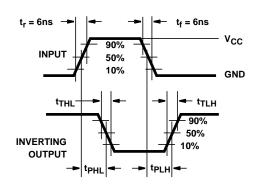


FIGURE 3. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

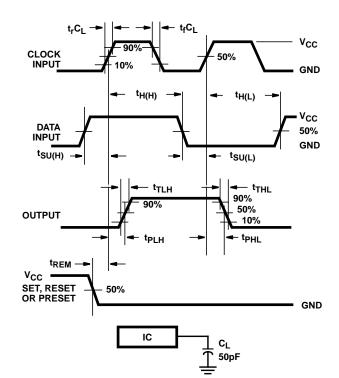
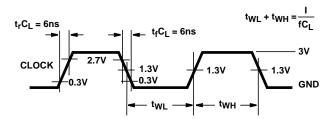


FIGURE 5. HC SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS



NOTE: Outputs should be switching from 10% V $_{CC}$ to 90% V $_{CC}$ in accordance with device truth table. For f $_{MAX}$, input duty cycle = 50%.

FIGURE 2. HCT CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

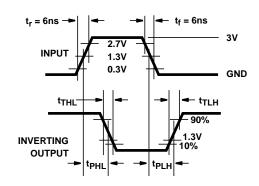


FIGURE 4. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

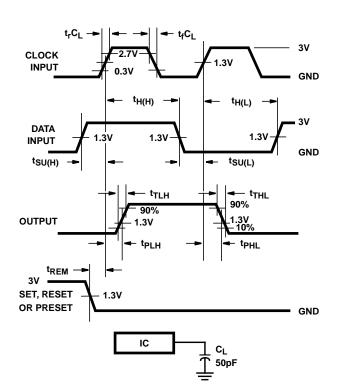


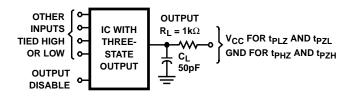
FIGURE 6. HCT SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

Test Circuits and Waveforms (Continued) 6ns 3V V_{CC} OUTPUT OUTPUT 90% **DISABLE** 50% DISABLE 10% 0.3 GND GND t_{PZL} → - t_{PLZ} → t_{PZL} ► t_{PLZ} → **OUTPUT LOW** OUTPUT LOW 50% TO OFF TO OFF 1.3V 10% 10% ◆ t_{PHZ} ◆ - t_{PZH} · t_{PHZ} → tpzh -90% 90% **OUTPUT HIGH OUTPUT HIGH** 50% TO OFF TO OFF 1.3V OUTPUTS **OUTPUTS OUTPUTS OUTPUTS OUTPUTS OUTPUTS ENABLED** ENABLED **DISABLED ENABLED**

FIGURE 7. HC THREE-STATE PROPAGATION DELAY **WAVEFORM**

DISABLED

FIGURE 8. HCT THREE-STATE PROPAGATION DELAY **WAVEFORM**



ENABLED

NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1 k\Omega$ to V_{CC} , $C_L = 50pF$.

FIGURE 9. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT





6-Feb-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type		Pins		Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
5962-8681401RA	ACTIVE	CDIP	J	20	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	5962-8681401RA CD54HC534F3A	Samples
5962-8681501RA	ACTIVE	CDIP	J	20	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	5962-8681501RA CD54HC564F3A	Samples
5962-8984901RA	ACTIVE	CDIP	J	20	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	5962-8984901RA CD54HCT534F3A	Samples
CD54HC534F3A	ACTIVE	CDIP	J	20	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	5962-8681401RA CD54HC534F3A	Samples
CD54HC564F3A	ACTIVE	CDIP	J	20	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	5962-8681501RA CD54HC564F3A	Samples
CD54HCT534F3A	ACTIVE	CDIP	J	20	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	5962-8984901RA CD54HCT534F3A	Samples
CD54HCT564F3A	ACTIVE	CDIP	J	20	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	CD54HCT564F3A	Samples
CD74HC534E	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC534E	Samples
CD74HC534EE4	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC534E	Samples
CD74HC564E	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC564E	Samples
CD74HC564M	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC564M	Samples
CD74HC564M96	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC564M	Samples
CD74HC564M96E4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC564M	Samples
CD74HCT534E	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT534E	Samples
CD74HCT564E	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT564E	Samples
CD74HCT564M	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT564M	Samples
CD74HCT564MG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT564M	Samples



6-Feb-2020

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF CD54HC534, CD54HC564, CD54HCT534, CD54HCT564, CD74HC534, CD74HC564, CD74HC534, CD74HC564, CD7

- Catalog: CD74HC534, CD74HC564, CD74HCT534, CD74HCT564
- Military: CD54HC534, CD54HC564, CD54HCT534, CD54HCT564

NOTE: Qualified Version Definitions:



PACKAGE OPTION ADDENDUM

6-Feb-2020

• Catalog - TI's standard catalog product

www.ti.com

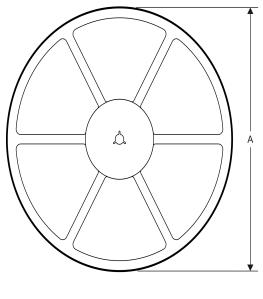
• Military - QML certified for Military and Defense Applications

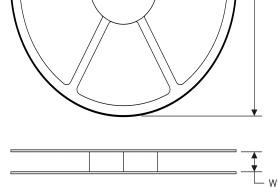
PACKAGE MATERIALS INFORMATION

14-Jul-2012 www.ti.com

TAPE AND REEL INFORMATION

REEL DIMENSIONS





TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC564M96	SOIC	DW	20	2000	330.0	24.4	10.8	13.0	2.7	12.0	24.0	Q1

PACKAGE MATERIALS INFORMATION

www.ti.com 14-Jul-2012



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HC564M96	SOIC	DW	20	2000	367.0	367.0	45.0

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.





SOIC



- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



14 LEADS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

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